Figure 3a depicts vertical measurement values of a wafer profile after etching with ethylene glycol/ HF 15% a spin etcher.

Figure 3b depicts horizontal measurement values of a wafer profile after etching with ethylene glycol/ HF 15% a spin etcher.

Figure 4a depicts vertical measurement values of a wafer profile after etching with ethylene glycol/glycerol/ HF 15% a spin etcher.

Figure 4b depicts horizontal measurement values of a wafer profile after etching with ethylene glycol/glycerol/ HF 15% a spin etcher.

IN THE CLAIMS

Please cancel claims 2, and 6:

Please amend claims 1, 3-5, and 7-8 as follows:

1. **(Amended)** An etching solution comprising 5- 20% by weight hydrofluoric acid, an organic solvent consisting essentially of, individually or as a mixture ethylene glycol, propylene glycol, ethanol, and glycerol, and 1-20 % by weight water for the production of integrated circuits.

3.**(Amended)** An etching solution according to claim 1, comprising only one ~~an~~ organic solvent selected from the group consisting of ethylene glycol, propylene glycol, ethanol, and glycerol.

4.**(Amended)** An Etching solution according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:10 to 10:1.

5. **(Amended)** An Etching solution according to Claim 1, comprising, as organic solvent, ethylene glycol and glycerol in a mixing ratio of from 1:5 to 5:1.

7. **(Amended)** An Etching solution according to Claim 1, comprising a mixture of high-purity individual components.

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8. **(Amended)** A method for the selective etching of doped silicate layers comprising treating said doped silicate layers with an etching solution according to Claim 1.

Please add the following new Claims:

9. **(New)** A method according to claim 8, wherein said doped silicate is boron doped glass.

10. **(New)** A method according to claim 8, wherein said doped silicate is phosphorous doped glass.

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11. **(New)** A method according to claim 8, wherein said doped silicate is boron- phosphorous doped glass.

12. **(New)** A method according to claim 8, wherein said selective etching is carried out in a spin etcher.

13. **(New)** A method according to claim 8, wherein said selective etching is carried out in a drip etcher.